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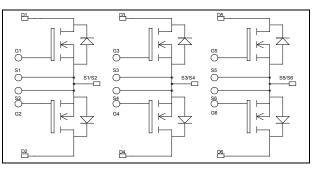
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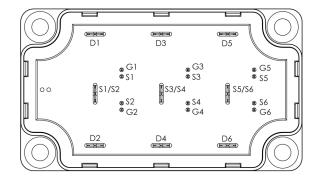
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Triple dual Common Source Super Junction MOSFET Power Module





Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V _{DSS}	Drain - Source Breakdown Voltage		800	V
I _D	Continuous Drain Current	$T_c = 25^{\circ}C$	28	
		$T_c = 80^{\circ}C$	21	А
I _{DM}	Pulsed Drain current		110	
V _{GS}	Gate - Source Voltage		±30	V
R _{DSon}	Drain - Source ON Resistance		150	mΩ
P _D	Maximum Power Dissipation $T_c = 25^{\circ}C$		277	W
I _{AR}	Avalanche current (repetitive and non repetitive)		17	А
E _{AR}	Repetitive Avalanche Energy		0.5	
E _{AS}	Single Pulse Avalanche Energy		670	mJ

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

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$V_{DSS} = 800V$ $R_{DSon} = 150m\Omega max @ Tj = 25^{\circ}C$ $I_{D} = 28A @ Tc = 25^{\circ}C$

Application

- AC Switches
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

Features

COOLNOS Power Semiconductors

- Ultra low R_{DSon}
- Low Miller capacitance
- Ultra low gate charge
- Avalanche energy rated
- Very rugged
- Kelvin source for easy drive
- Very low stray inductance
 - Symmetrical design
 - Lead frames for power connections
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Very low (12mm) profile
- Each leg can be easily paralleled to achieve a dual common source configuration of three times the current capability
- RoHS Compliant

1 - 7



All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
I _{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 800V$ $T_j = 25^{\circ}C$			50	μA
		$V_{GS} = 0V, V_{DS} = 800V$ $T_j = 125^{\circ}C$			375	
R _{DS(on)}	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 14A$			150	mΩ
V _{GS(th)}	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 2mA$	2.1	3	3.9	V
I _{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 20 V, V_{DS} = 0V$			±150	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
C _{iss}	Input Capacitance	$V_{GS} = 0V$		4507		
C _{oss}	Output Capacitance	$V_{\rm DS} = 25 V$		2092		pF
C _{rss}	Reverse Transfer Capacitance	f = 1 MHz		108		
Qg	Total gate Charge	$V_{GS} = 10V$		180		
Q _{gs}	Gate – Source Charge	$V_{Bus} = 400 V$		22		nC
Q_{gd}	Gate – Drain Charge	$I_D = 28A$		90		
T _{d(on)}	Turn-on Delay Time	Inductive switching @125°C		10		
T _r	Rise Time	$V_{GS} = 15V$		13		
T _{d(off)}	Turn-off Delay Time	$V_{Bus} = 533V$ $I_D = 28A$		83		ns
T_{f}	Fall Time	$R_G = 2.5\Omega$		35		
Eon	Turn-on Switching Energy	Inductive switching @ 25°C		486		т
E _{off}	Turn-off Switching Energy	$V_{GS} = 15V, V_{Bus} = 533V$ $I_D = 28A, R_G = 2.5\Omega$		278		μJ
Eon	Turn-on Switching Energy	Inductive switching @ 125°C		850		т
E _{off}	Turn-off Switching Energy	$V_{GS} = 15V, V_{Bus} = 533V$ $I_D = 28A, R_G = 2.5\Omega$		342		μJ

Source - Drain diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
Is	Continuous Source current		$Tc = 25^{\circ}C$		28		
	(Body diode)		$Tc = 80^{\circ}C$		21		А
V _{SD}	Diode Forward Voltage	$V_{GS} = 0V, I_S = -28A$				1.2	V
dv/dt	Peak Diode Recovery 1					6	V/ns
t _{rr}	Reverse Recovery Time	$I_s = -28A$	$T_j = 25^{\circ}C$		550		ns
Q _{rr}	Reverse Recovery Charge	$V_{\rm R} = 400V$ $di_{\rm S}/dt = 200 {\rm A}/\mu {\rm s}$	$T_j = 25^{\circ}C$		30		μC

• dv/dt numbers reflect the limitations of the circuit rather than the device itself. Is 7

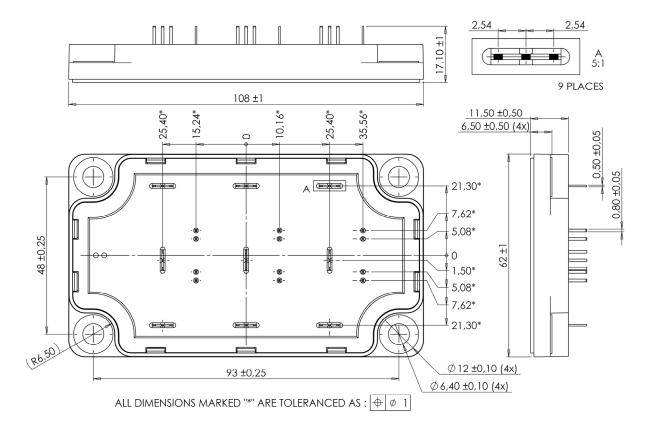
$$V_{\rm S} \leq -28 A$$
 di/dt $\leq 200 A/\mu s$ $V_{\rm R} \leq V_{\rm DSS}$ $T_{\rm j} \leq 150^{\circ} C$



Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
R _{thJC}	Junction to Case Thermal Resistance					0.45	°C/W
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T _J	Operating junction temperature range			-40		150	
T _{STG}	Storage Temperature Range			-40		125	°C
T _C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M6	3		5	N.m
Wt	Package Weight					250	g

SP6-P Package outline (dimensions in mm)

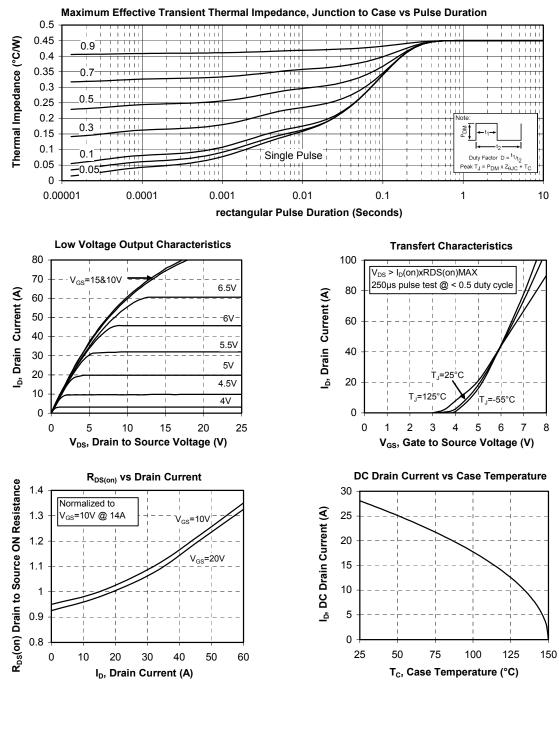


See application note 1902 - Mounting Instructions for SP6-P (12mm) Power Modules on www.microsemi.com



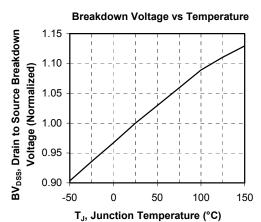
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Typical Performance Curve

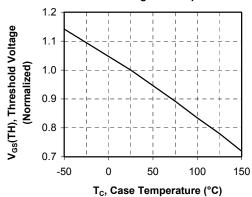


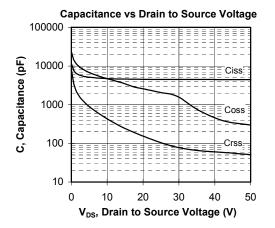
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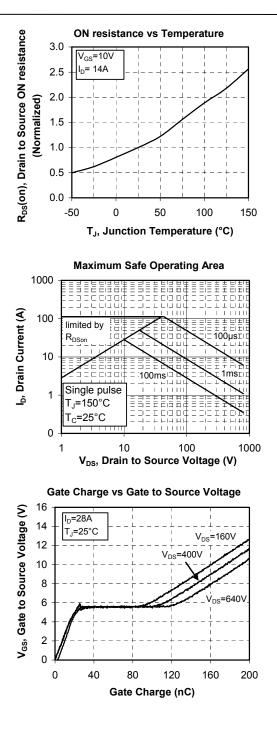








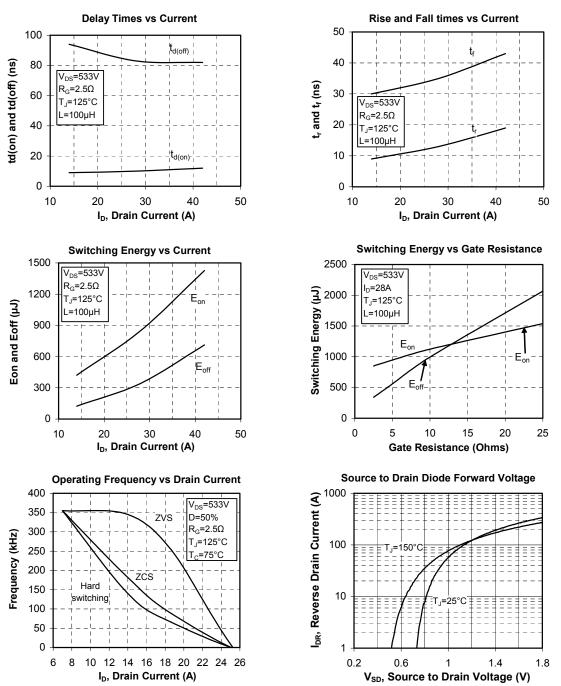




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